

## **AMENDMENTS TO THE SPECIFICATION**

**Please insert a paragraph beginning at page 1, line 5:**

### **CROSS REFERENCE TO RELATED APPLICATION**

The present application is a 35 U.S.C. § 371 national phase conversion of PCT/JP2003/016679, filed 25 December 2003, which claims priority to Japanese Patent Application No: 2003-3131, filed 9 January 2003. The PCT International Application was published in the Japanese language.

**Please replace the paragraph beginning at page 3, line 7, with the following rewritten paragraph:**

According to the present invention, the substrate processing system comprises: a collection ~~means~~ part for monitoring and collecting a plurality of control elements in a specific step as one of processes of the predetermined processing in the substrate processing apparatus; and an abnormality detection ~~means~~ part for detecting a processing abnormality in the substrate processing apparatus based on the plurality of control elements collected by the collection ~~means~~ part.

**Please replace the paragraph beginning at page 3, line 18, with the following rewritten paragraph:**

According to one aspect of the present invention, the substrate processing apparatus discharges a cleaning solution and thereafter discharges pure water onto a rotating substrate to perform cleaning of the substrate, the collection ~~means~~ part monitors and collects a plurality of control elements in a cleaning solution spread step in which the cleaning solution is discharged and spread to coat a rotating substrate, and the abnormality detection ~~means~~ part detects a processing abnormality in the cleaning based on a combination of two or more of the plurality of control elements in the cleaning solution spread step including the number of revolutions of a substrate, the temperature, flow rate and concentration of a cleaning solution, and cleaning solution discharge time.

**Please replace the paragraph beginning at page 4, line 9, with the following rewritten paragraph:**

According to the present invention, the substrate processing apparatus comprises: a collection means part for monitoring and collecting a plurality of control elements in a specific step as one of processes of the predetermined processing; and an abnormality detection means part for detecting a processing abnormality in the processes based on the plurality of control elements collected by the collection ~~means~~ part.

**Please replace the paragraph beginning at page 4, line 18, with the following rewritten paragraph:**

According to one aspect of the present invention, the predetermined processing is cleaning by discharging a cleaning solution and thereafter discharging pure water onto a rotating substrate to clean the substrate, the collection ~~means~~ part monitors and collects a plurality of control elements in a cleaning solution spread step in which the cleaning solution is discharged and spread to coat a rotating substrate, and the abnormality detection ~~means~~ part detects a processing abnormality in the cleaning based on a combination of two or more of the plurality of control elements in the cleaning solution spread step including the number of revolutions of a substrate, the temperature, flow rate and concentration of a cleaning solution, and cleaning solution discharge time.

**Please replace the paragraph beginning at page 30, line 6, with the following rewritten paragraph:**

The etching solution supply part ~~63~~ 163 has the motor 73 provided outside the chamber 65, the arm 74 caused to pivot by the pivotal motion of the motor 73, and etching solution nozzle 175 provided to an end of the arm 74 and serving to downwardly discharge an etching solution, a weighing bath 100 for preparing and storing an etching solution of a prescribed concentration, and the pump 77 for feeding an etching solution from the weighing bath 100 toward the etching solution nozzle 175. A conduit is communicatively connected between the etching solution nozzle 175 and the weighing bath 100. An etching solution valve 188 and a filter 89 for purifying an etching solution

are interposed in this conduit. The flowmeter 30c, the thermometer 30d and a concentration meter 30f are further imposed in the conduit to respectively detect the flow rate, the temperature and the concentration of an etching solution passing through the conduit.

**Please replace the paragraph beginning at page 47, line 23 , with the following rewritten paragraph:**

Alternatively, the etching processing unit MP of the second embodiment may be incorporated into Fig 12 in place of the removal processing unit SR to perform a series of process steps substantially the same as discussed in the second embodiment (Figs. 10 and 11) in the substrate processing apparatus 3B. That is, the substrate processing apparatus 3B follows the process sequence in etching exactly the same as that discussed with reference to Fig. 10. In the etching solution discharge and spread step (step S12) and in the pure water discharge step (step S14), the CPU 301 collects data indicative of a plurality of control elements and detects a processing abnormality in the substrate processing apparatus 3B based on the collected data of each control element. In the etching solution discharge and spread step, a combination of the number of revolutions of a substrate, the temperature, flow rate and concentration of an etching solution, and ~~removal~~ etching solution discharge time is synthetically asses to detect a processing abnormality. In pure water discharge step, a combination of the number of revolutions of a substrate, the flow rate of pure water and pure water discharge time is synthetically assessed to detect a processing abnormality.